

# N-Channel Enhancement-Mode Vertical DMOS FET

#### **Features**

- · 2V Maximum Low Threshold
- · High Input Impedance
- · 125 pF Maximum Low Input Capacitance
- · Fast Switching Speeds
- · Low On-Resistance
- · Free from Secondary Breakdown
- · Low Input and Output Leakage

### **Applications**

- Logic-Level Interfaces (Ideal for TTL and CMOS)
- · Solid-State Relays
- · Battery-Operated Systems
- · Photovoltaic Drives
- · Analog Switches
- · General Purpose Line Drivers
- · Telecommunication Switches

#### **General Description**

The TN2524 low-threshold Enhancement-mode (normally-off) transistor uses a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

#### Package Type



See Table 3-1 for pin information.

#### 1.0 ELECTRICAL CHARACTERISTICS

### **Absolute Maximum Ratings†**

Drain-to-Source Voltage	BV <sub>DSS</sub>
Drain-to-Gate Voltage	
Gate-to-Source Voltage	
Operating Ambient Temperature, T <sub>A</sub>	
Storage Temperature, T <sub>S</sub>	

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS

**Electrical Specifications:**  $T_A = 25^{\circ}$ C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 µs pulse, 2% duty cycle

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions
Drain-to-Source Breakdown Voltage	BV <sub>DSS</sub>	240	_	_	V	$V_{GS} = 0V$ , $I_D = 2 \text{ mA}$
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.6	_	2	V	$V_{GS} = V_{DS}$ , $I_D = 1 \text{ mA}$
Change in V <sub>GS(th)</sub> with Temperature	$\Delta V_{GS(th)}$	_		<b>–</b> 5	mV/°C	$V_{GS} = V_{DS}$ , $I_D = 1 \text{ mA}$ (Note 1)
Gate Body Leakage Current	I <sub>GSS</sub>		_	100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
				10	μΑ	V <sub>GS</sub> = 0V, V <sub>DS</sub> = Maximum rating
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>			1	mA	$V_{DS}$ = 0.8 Maximum rating, $V_{GS}$ = 0V, $T_A$ = 125°C (Note 1)
On-State Drain Current	1	0.5	1.9		Α	$V_{GS} = 4.5V, V_{DS} = 25V$
On-State Drain Current	I <sub>D</sub> (ON)	1	2.8	_	Α	$V_{GS} = 10V, V_{DS} = 25V$
Static Drain-to-Source On-State Resistance	D	_	4	6	Ω	$V_{GS}$ = 4.5V, $I_{D}$ = 250 mA
Static Diani-to-Source Oil-State Resistance	R <sub>DS(ON)</sub>		4	6	Ω	$V_{GS} = 10$ , $I_D = 500$ mA
Change in R <sub>DS(ON)</sub> with Temperature	ΔR <sub>DS(ON)</sub>	_	_	1.4	%/°C	V <sub>GS</sub> = 10V, I <sub>D</sub> = 500 mA ( <b>Note 1</b> )

Note 1: Specification is obtained by characterization and is not 100% tested.

# **AC ELECTRICAL CHARACTERISTICS**

<b>Electrical Specifications:</b> T <sub>A</sub> = 25°C unless otherwise specified. All AC parameters are not 100% sample tested.									
Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions			
Forward Transconductance	G <sub>FS</sub>	300	600	_	mmho	V <sub>DS</sub> = 25V, I <sub>D</sub> = 500 mA			
Input Capacitance	C <sub>ISS</sub>	_	65	125	pF	V <sub>GS</sub> = 0V,			
Common-Source Output Capacitance	Coss	_	35	70		V <sub>DS</sub> = 25V,			
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	10	25	pF	f = 1 MHz			
Turn-On Delay Time	t <sub>d(ON)</sub>	_	_	10	ns				
Rise Time		_	_	10	ns	$V_{DD} = 25V,$			
Turn-Off Delay Time		_	_	20	ns	I <sub>D</sub> = 1A,   R <sub>GEN</sub> = 25Ω			
Fall Time		_	_	20	ns	GEN			
DIODE PARAMETER									
Diode Forward Voltage Drop	V <sub>SD</sub>	_	_	1.8	V	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 1A ( <b>Note 1</b> )			
Reverse Recovery Time	t <sub>rr</sub>	_	300	_	ns	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 1A			

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 μs pulse, 2% duty cycle

# **TEMPERATURE SPECIFICATIONS**

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions
TEMPERATURE RANGE						
Operating Ambient Temperature	T <sub>A</sub>	-55	_	+150	°C	
Storage Temperature	T <sub>S</sub>	-55	_	+150	°C	
PACKAGE THERMAL RESISTANCE						
3-lead SOT-89		_	73	_	°C/W	

### THERMAL CHARACTERISTICS

Package	I <sub>D</sub> (Note 1) (Continuous) (mA)	I <sub>D</sub> (Pulsed) (A)	Power Dissipation at T <sub>A</sub> = 25°C (Note 2) (W)	I <sub>DR</sub> (Note 1) (mA)	I <sub>DRM</sub> (A)
3-lead SOT-89	360	2	1.6	360	2

Note 1:  $I_D$  (continuous) is limited by maximum rated  $T_J$ .

<sup>2:</sup> T<sub>A</sub> = 25°C. Mounted on an FR5 Board, 25 mm x 25 mm x 1.57 mm.

### 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

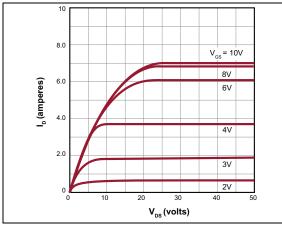


FIGURE 2-1: Output Characteristics.

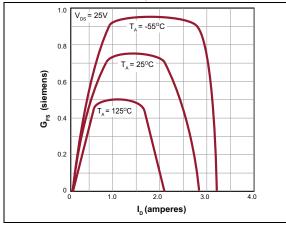
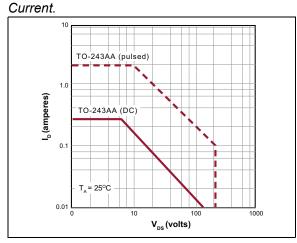


FIGURE 2-2: Transconductance vs. Drain



**FIGURE 2-3:** Maximum Rated Safe Operating Area.

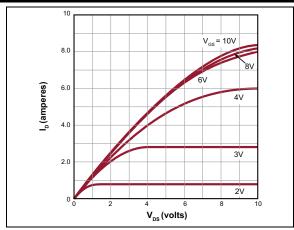
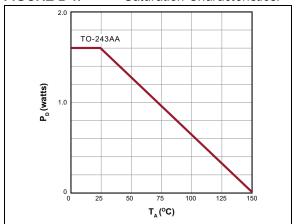
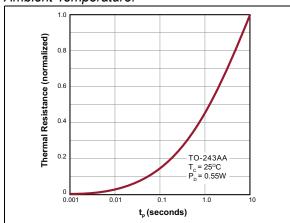


FIGURE 2-4: Saturation Characteristics.



**FIGURE 2-5:** Power Dissipation vs. Ambient Temperature.



**FIGURE 2-6:** Thermal Response Characteristics.

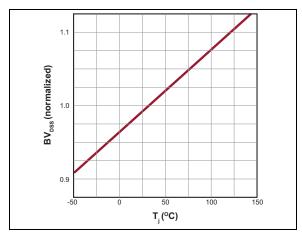


FIGURE 2-7: Temperature.

 $BV_{DSS}$  Variation with

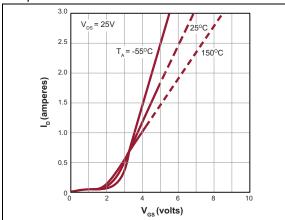
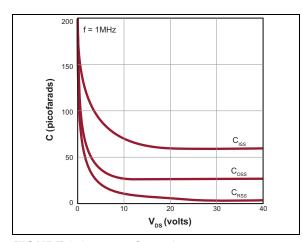


FIGURE 2-8:

Transfer Characteristics.



**FIGURE 2-9:** Capacitance vs. Drain-to-Source Voltage.

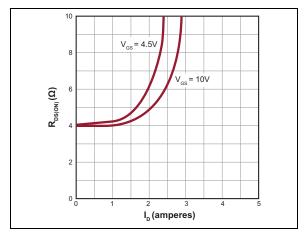


FIGURE 2-10:

On-Resistance vs. Drain

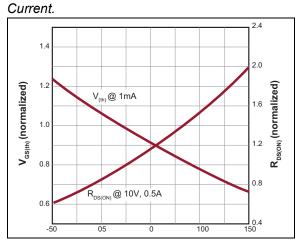


FIGURE 2-11: Temperature.

 $V_{GS(th)}$  and  $R_{DS(ON)}$  with

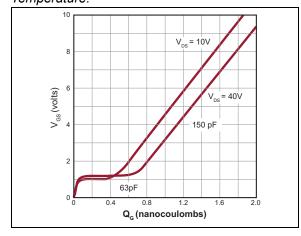


FIGURE 2-12: Characteristics.

Gate Drive Dynamic

# TN2524

# 3.0 PIN DESCRIPTION

Table 3-1 shows details on the pins of TN2524. Refer to **Package Type** for the location of the pins.

TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Gate	Gate
2,4	Drain	Drain
3	Source	Source

# 4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for TN2524.

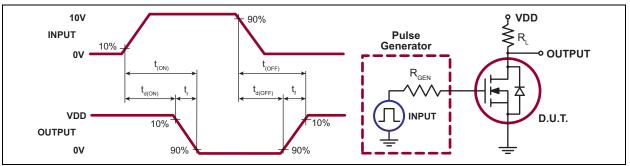


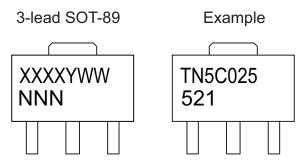
FIGURE 4-1: Switching Waveforms and Test Circuit.

TABLE 4-1: PRODUCT SUMMARY

BV <sub>DSS</sub> /BV <sub>DGS</sub> (V)	R <sub>DS(ON)</sub> (Maximum) (Ω)	I <sub>D(ON)</sub> (Minimum) (A)	V <sub>GS(TH)</sub> (Maximum) (V)
240	6	1	2

#### 5.0 PACKAGING INFORMATION

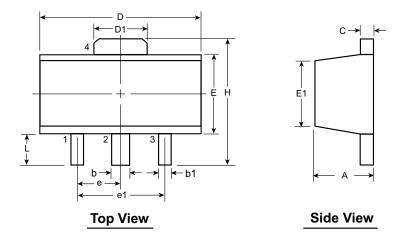
# 5.1 Package Marking Information



Legend: XX...X Product Code or Customer-specific information
Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')
NNN Alphanumeric traceability code
Pb-free JEDEC® designator for Matte Tin (Sn)
\* This package is Pb-free. The Pb-free JEDEC designator (e3)
can be found on the outer packaging for this package.

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

# 3-Lead TO-243AA (SOT-89) Package Outline (N8)



Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symbo	ol	Α	b	b1	С	D	D1	E	E1	е	e1	Н	L
	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.00 <sup>†</sup>			3.94	0.73 <sup>†</sup>
Dimensions (mm)	NOM	-	-	-	-	-	-	-	-	1.50 BSC	3.00 BSC	-	-
()	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986. † This dimension differs from the JEDEC drawing

Drawings not to scale.

# TN2524

NOTES:

# **APPENDIX A: REVISION HISTORY**

# **Revision A (November 2020)**

- Converted Supertex Doc# DSFP-TN2524 to Microchip DS20005952A
- · Changed the package marking format
- Made minor text changes throughout the document

# PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO.	XX		- <u>x</u> - <u>x</u>	Example:	
Device	Packa Optio		Environmental Media Type	a) TN2524N8-G:	N-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead SOT-89, 2000/Reel
Device:	TN2524	=	N-Channel Enhancement-Mode Vertical DMOS FET		
Package:	N8	=	3-lead SOT-89		
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package		
Media Type:	(blank)	=	2000/Reel for an N8 Package		

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ISBN: 978-1-5224-7123-3



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